

Device Modeling Report

COMPONENTS: Power MOSFET (Professional)
PART NUMBER: 2SK3565
MANUFACTURER: TOSHIBA
Body Diode (Professional) / ESD Protection Diode



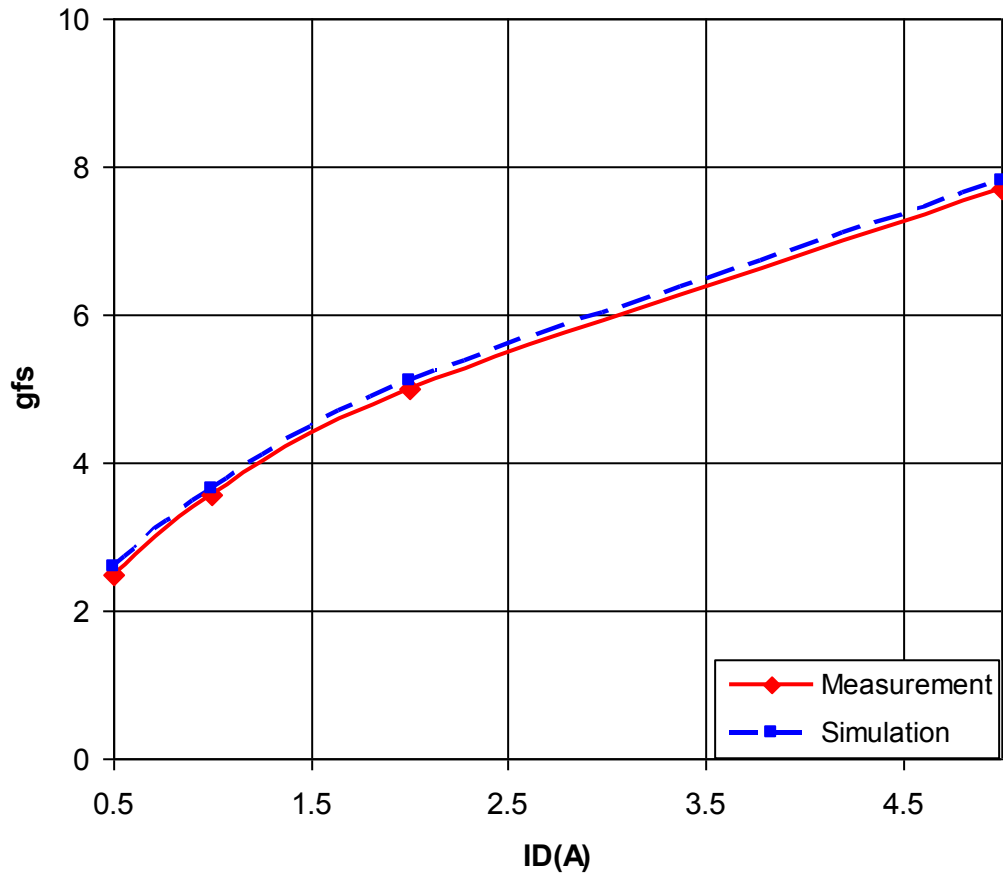
Bee Technologies Inc.

MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

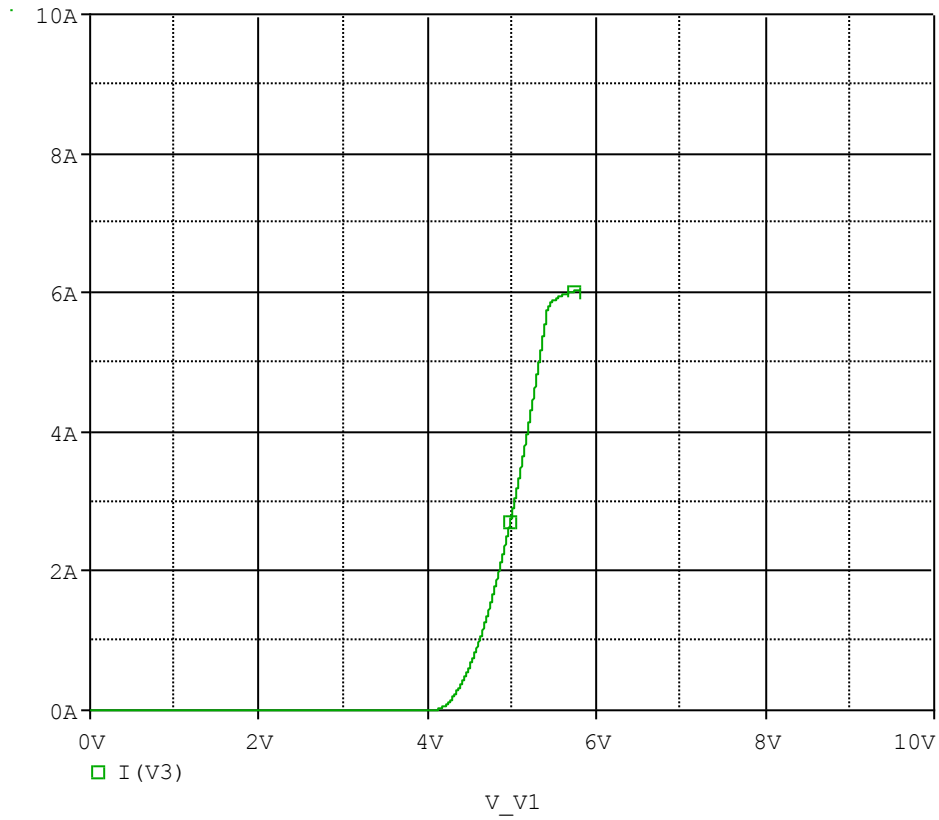


Comparison table

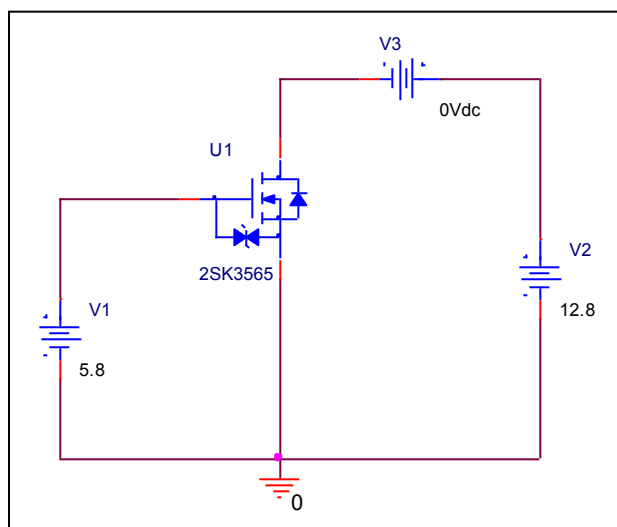
Id(A)	gfs		Error(%)
	Measurement	Simulation	
0.5	2.5	2.604	4.160
1	3.571	3.650	2.212
2	5	5.102	2.040
5	7.692	7.812	1.560

V_{gs}-I_d Characteristic

Circuit Simulation result

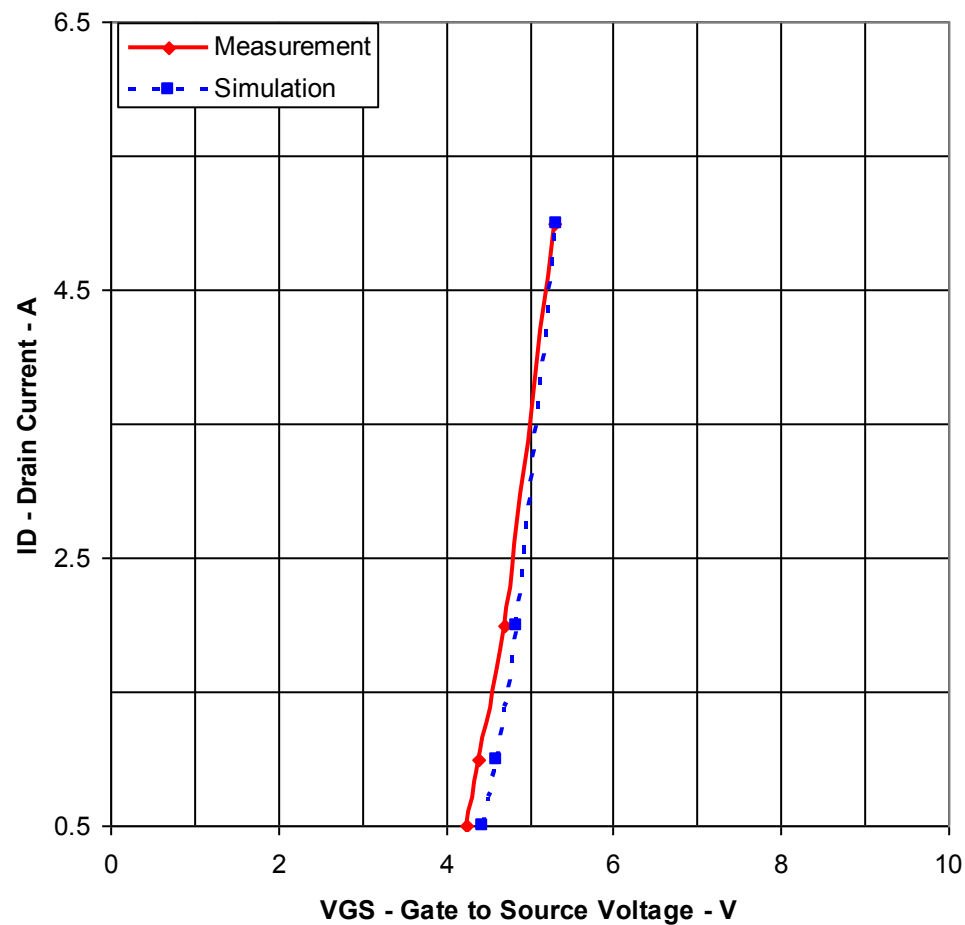


Evaluation circuit



Comparison Graph

Circuit Simulation Result

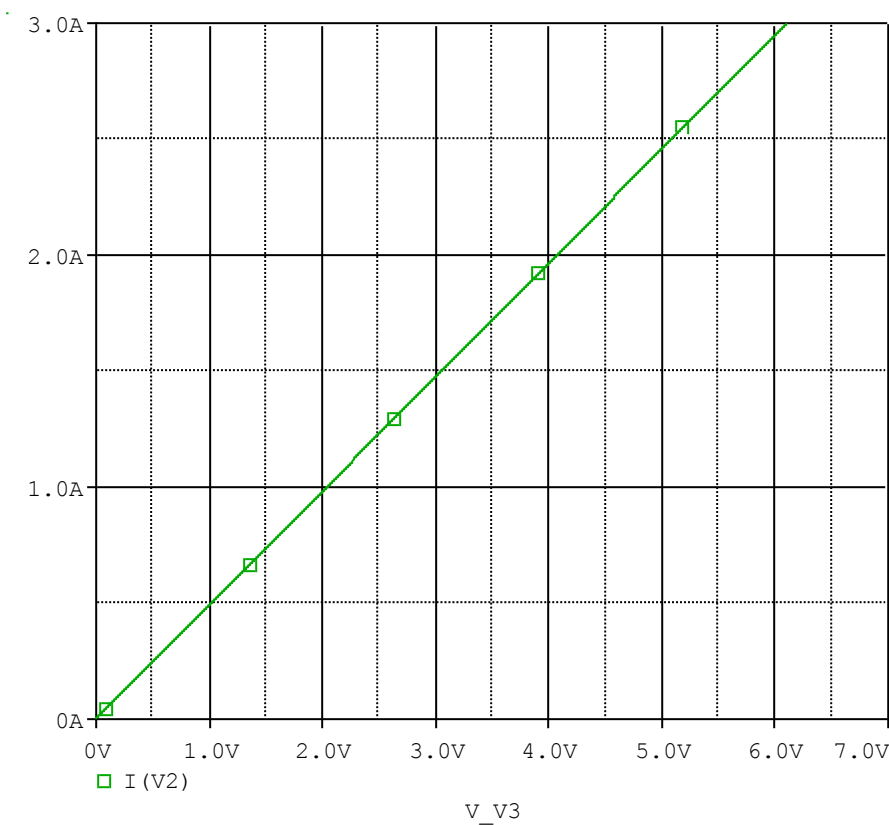


Simulation Result

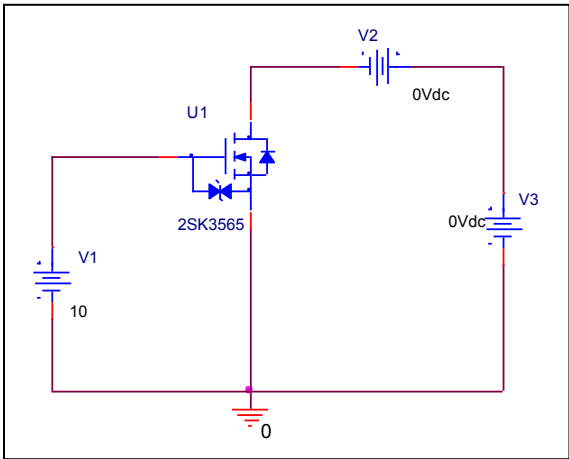
ID(A)	VGS(V)		Error (%)
	Measurement	Simulation	
0.5	4.25	4.449	4.682
1	4.4	4.6123	4.825
2	4.7	4.8462	3.111
5	5.3	5.3202	0.381

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

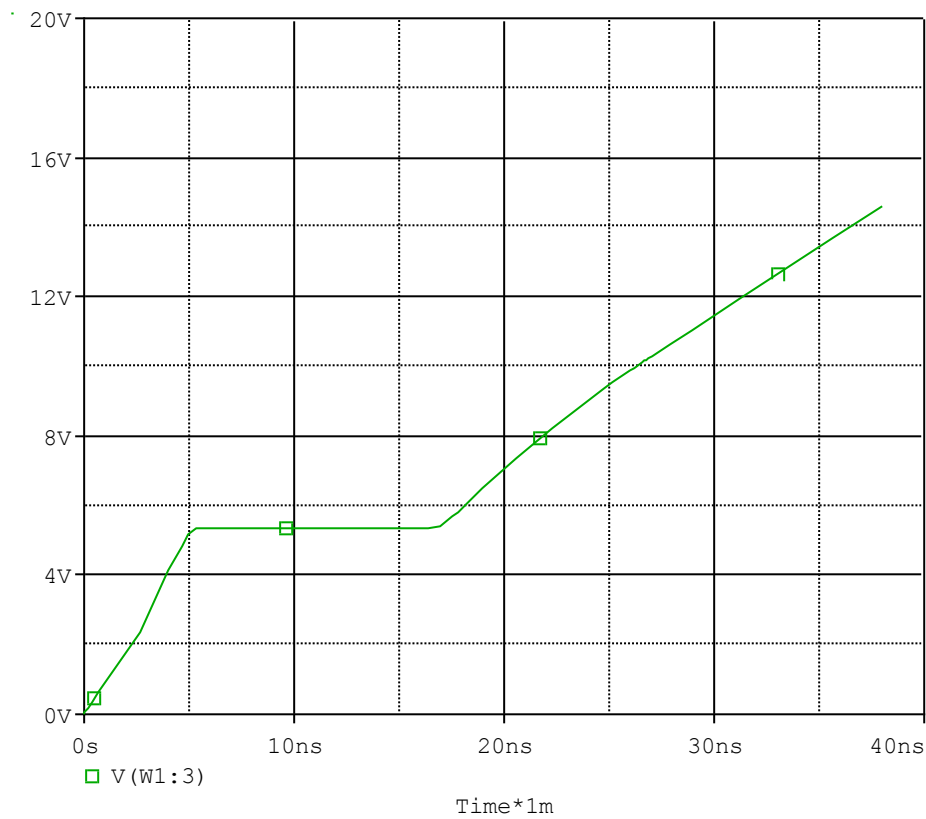


Simulation Result

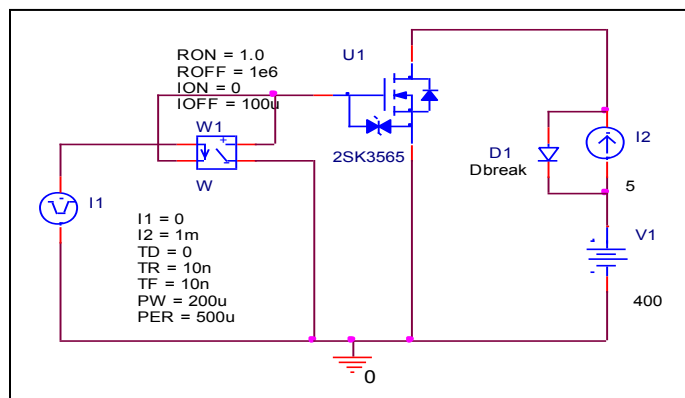
$I_D=3A, V_{GS}=10V$	Measurement		Simulation		Error (%)
$R_{DS(on)}$	2	Ω	2.035	Ω	1.75

Gate Charge Characteristic

Circuit Simulation result



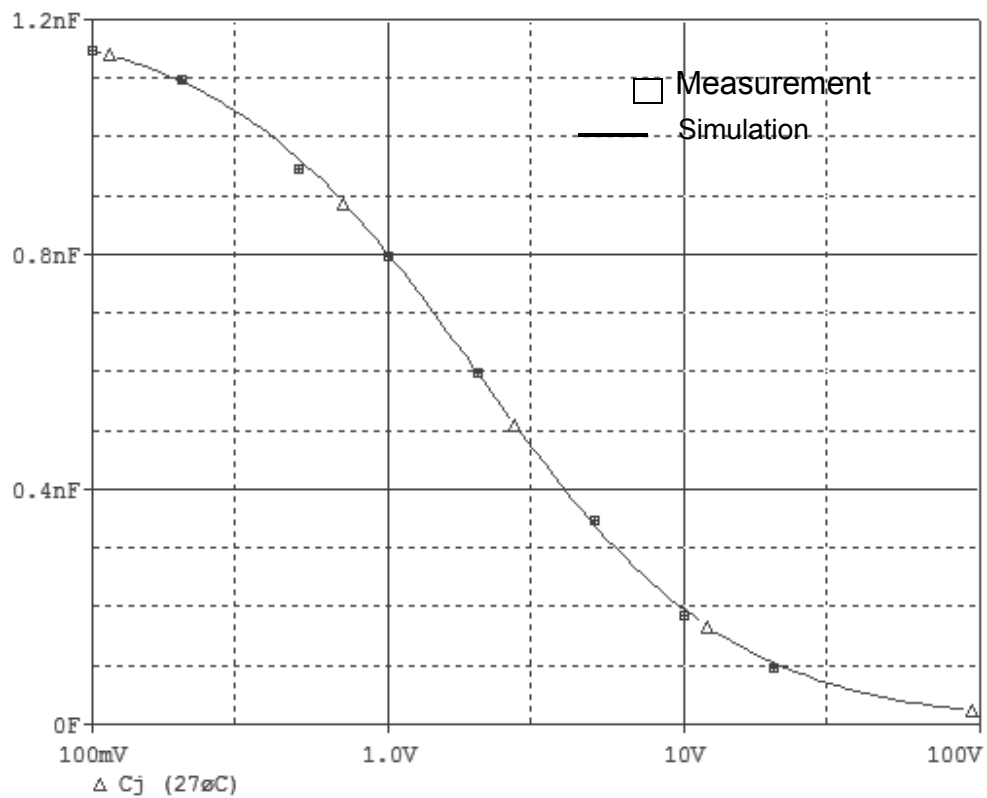
Evaluation circuit



Simulation Result

$V_{DD}=400V, I_D=5A$	Measurement		Simulation		Error (%)
Q_{gs}	5.2	nC	5.2633	nC	1.217
Q_{gd}	11.3	nC	11.350	nC	0.442
Q_g	26	nC	26.231	nC	0.888

Capacitance Characteristic

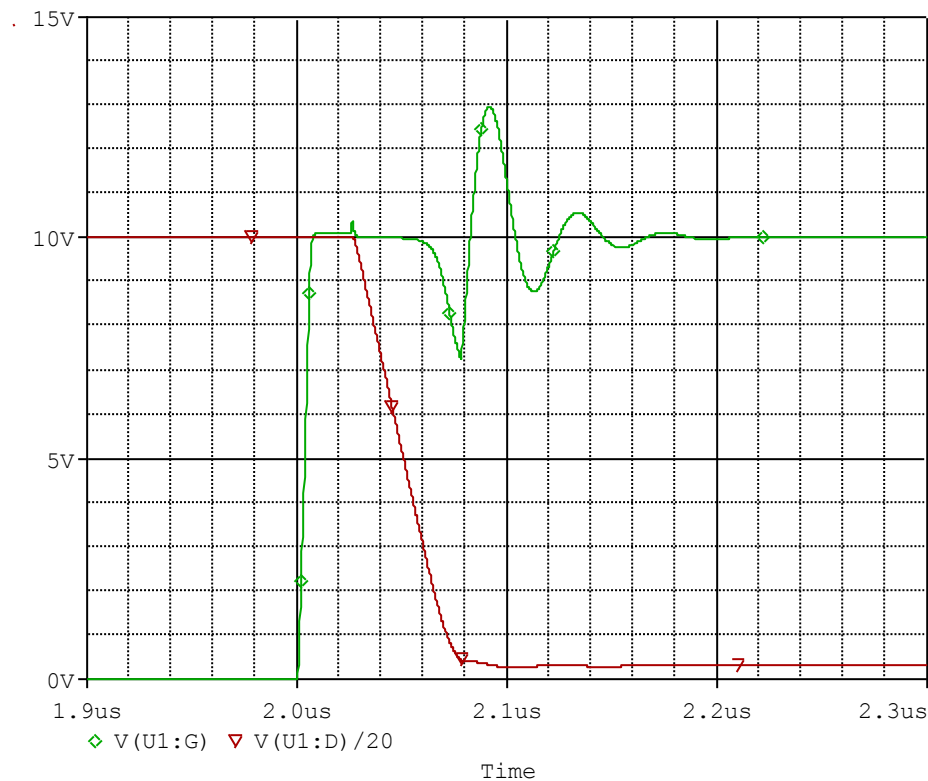


Simulation Result

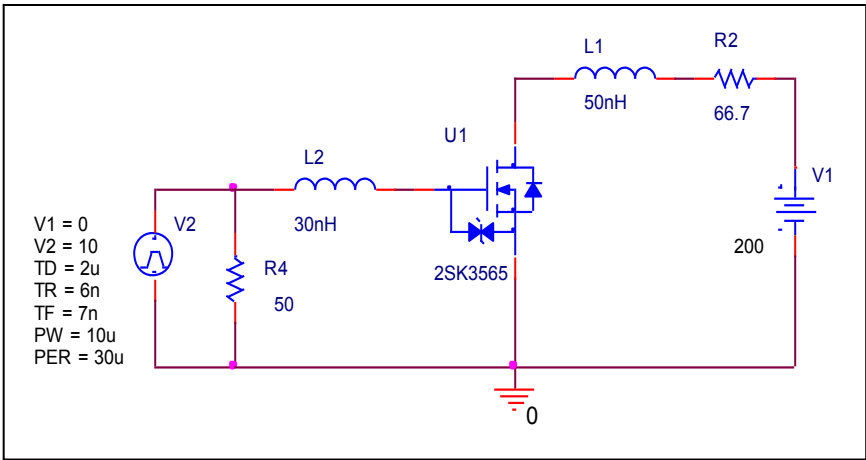
V _{DS} (V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.1	1150	1145	-0.435
0.2	1100	1095	-0.455
0.5	950	960	1.053
1	800	800	0.000
2	600	598	-0.333
5	350	340	-2.857
10	190	195	2.632
20	100	105	5

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

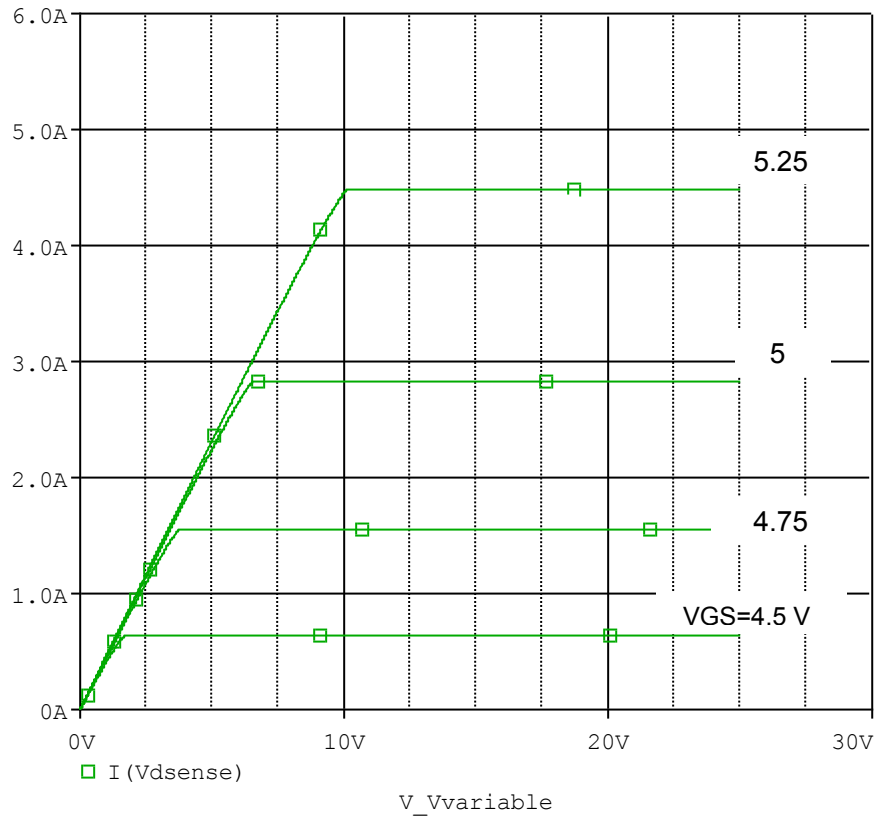


Simulation Result

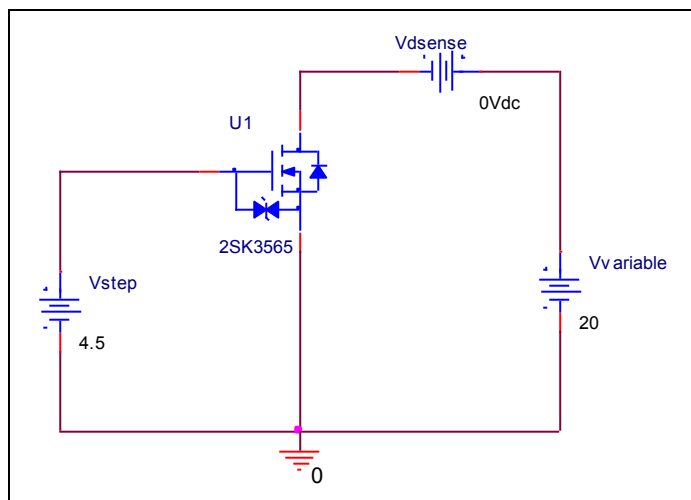
$I_D=3\text{ A}$, $V_{DD}=200\text{ V}$ $V_{GS}=0/10\text{ V}$	Measurement		Simulation		Error(%)
	ton	70.000 ns	70.110 ns	ns	
					0.157

Output Characteristic

Circuit Simulation result

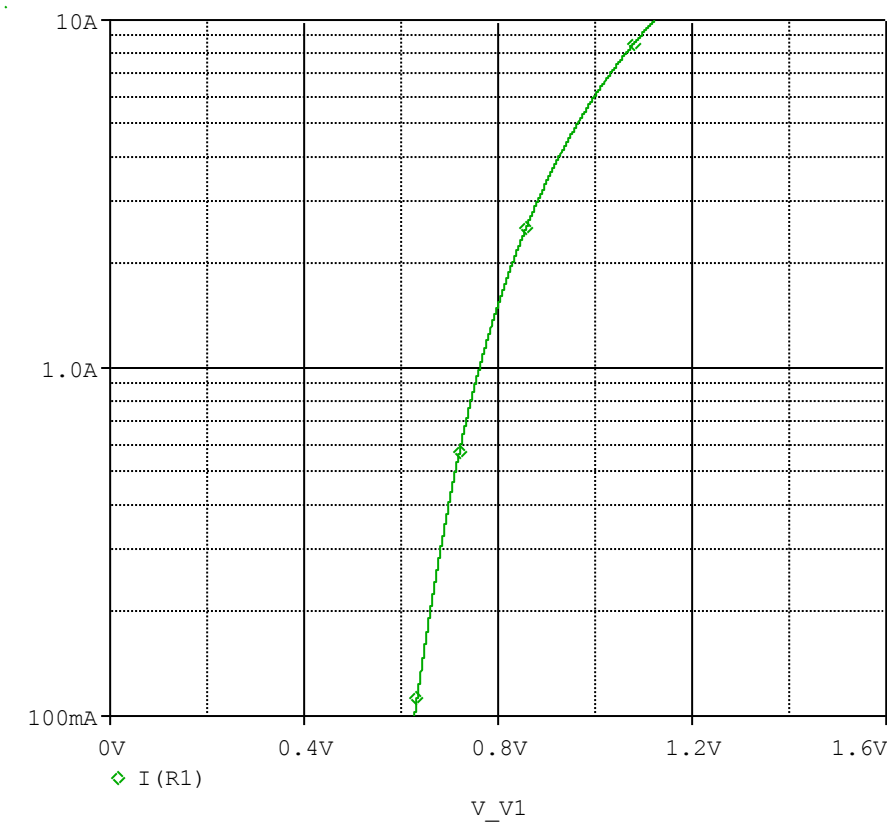


Evaluation circuit

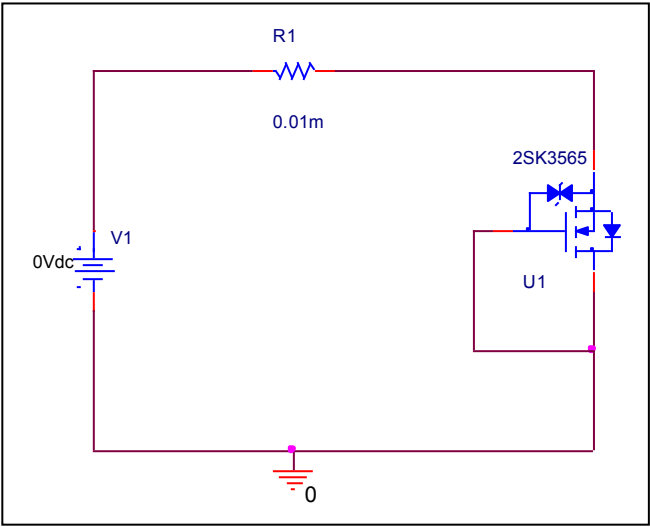


Forward Current Characteristic

Circuit Simulation Result

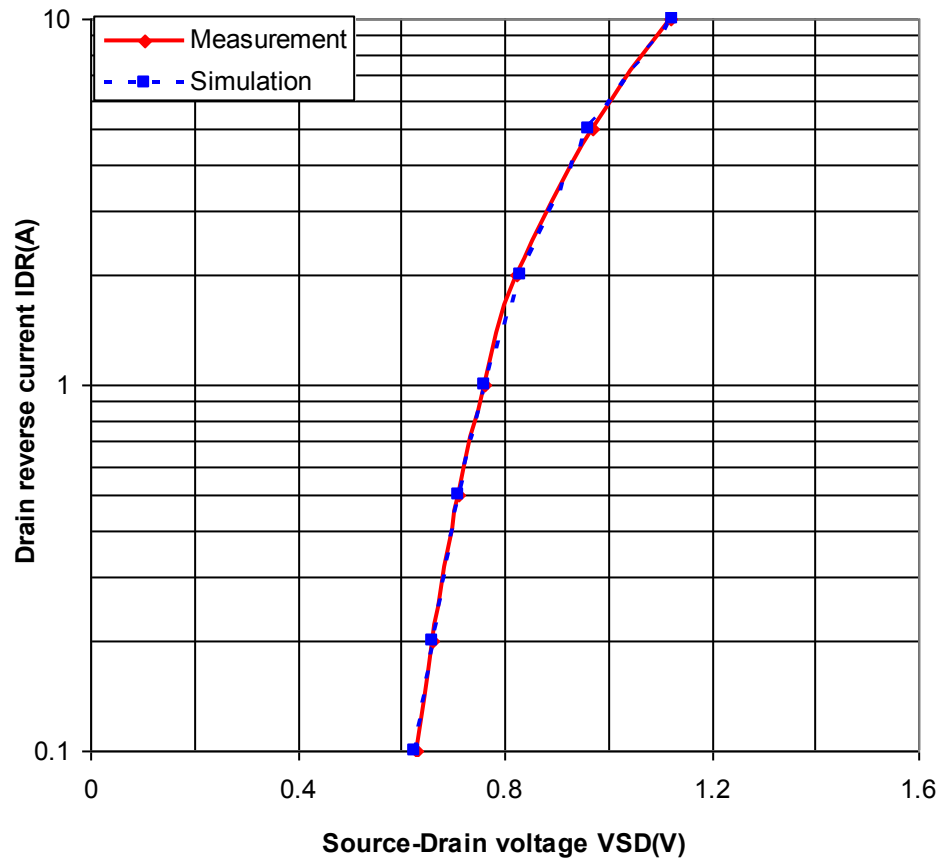


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

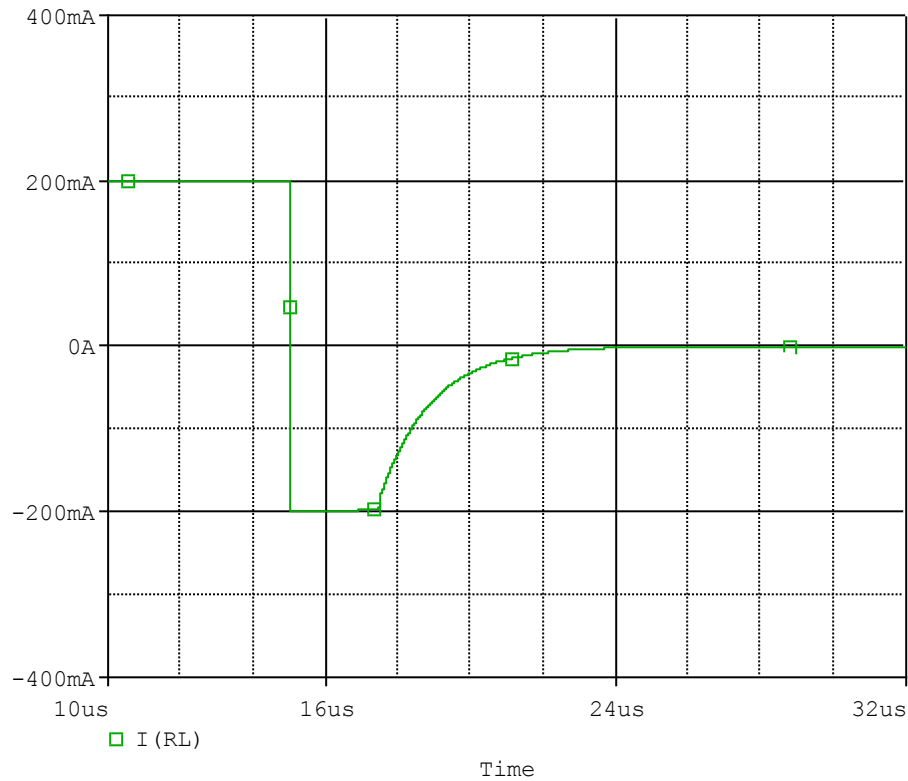


Simulation Result

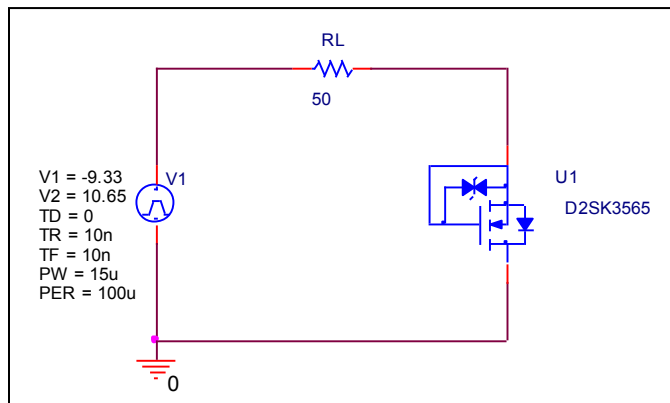
Ifwd(A)	VSD(V)		%Error
	Measuremen	Simulation	
0.1	0.63	0.628	-0.317
0.2	0.66	0.660	0
0.5	0.71	0.711	0.141
1	0.76	0.762	0.263
2	0.825	0.829	0.485
5	0.97	0.962	-0.825
10	1.12	1.123	0.268

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

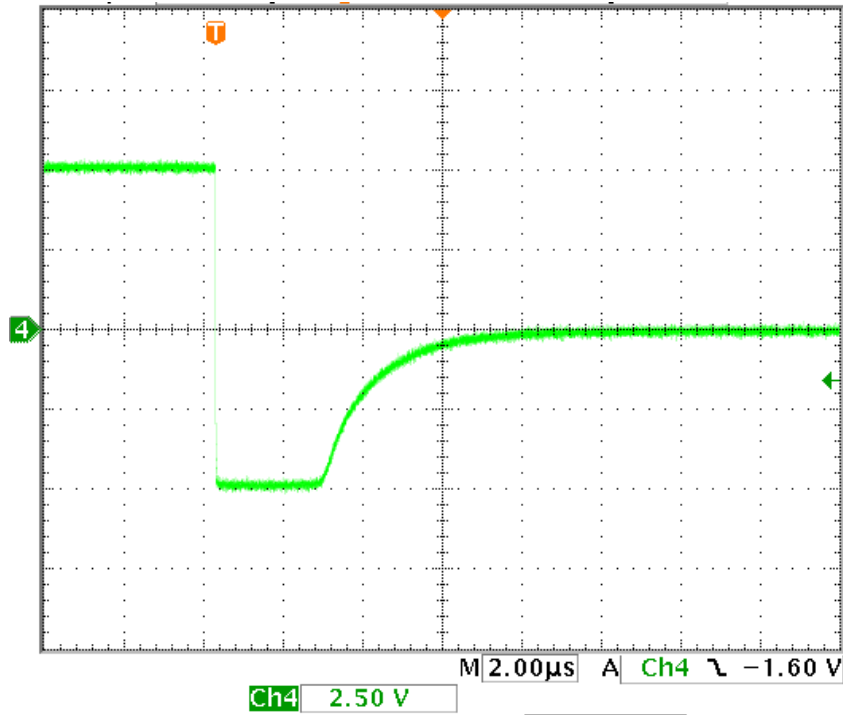


Compare Measurement vs. Simulation

	Measurement	Simulation	Error (%)
Trj(us)	2.4	2.402	0.083
Trb(us)	3.28	3.266	-0.427
Trr(us)	5.68	5.668	-0.211

Reverse Recovery Characteristic

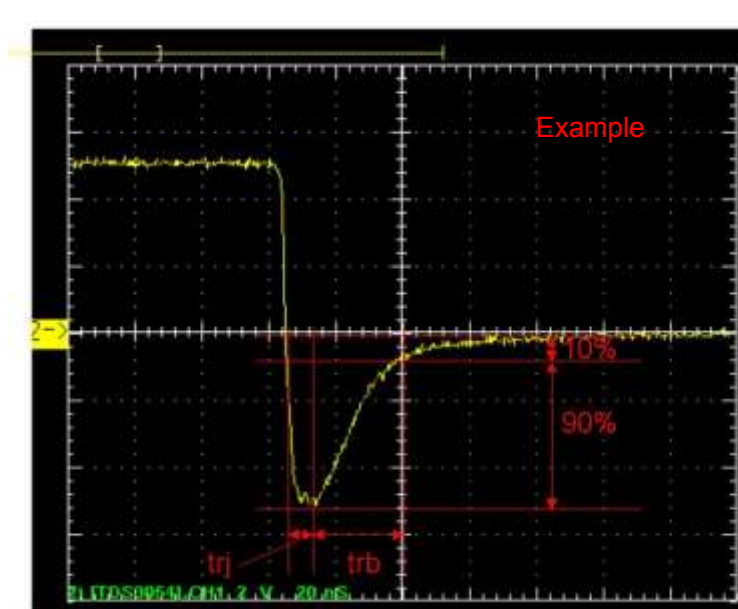
Reference



$T_{rr}=2.4(\mu s)$

$T_{rb}=3.28(\mu s)$

Conditions: $I_{fwd}=I_{rev}=0.2(A)$, $R_I=50$

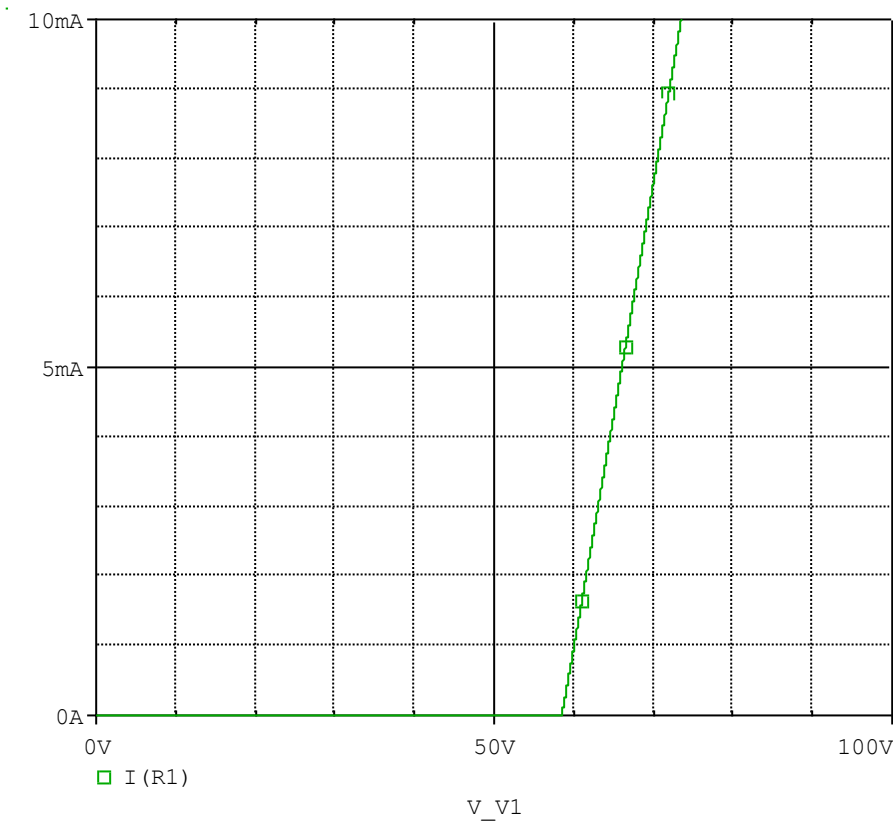


Relation between t_{rr} and t_{rb}

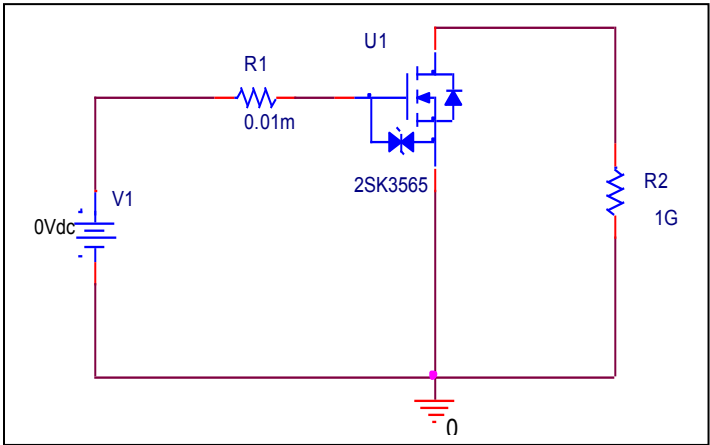
ESD PROTECTION DIODE

Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic

Reference

